## NSN 5961-01-414-5833

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**Fiig:** A110a0



View Online at https://aerobasegroup.com/nsn/5961-01-414-5833 **Inclosure Material:** Metal **Internal Configuration:** Field effect Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-236ab **Mounting Method:** Terminal Semiconductor Material: Silicon Voltage Rating In Volts Per Characteristic: 30.0 drain to source voltage **Current Rating Per Characteristic:** 10.00 milliamperes gate current **Terminal Type And Quantity:** 3 bonding pad Shelf Life: N/a **Unit Of Measure: Demilitarization:** No